

#### 40V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

## **Product Summary**

BVDSS	Ros(on) Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
-40V	$25m\Omega$ @ V <sub>GS</sub> = -10V	- 7.2A
	$45 \text{m}\Omega$ @ $V_{GS} = -4.5 \text{V}$	- 5.4A

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Backlighting
- DC-DC Converters
- Printer Equipment

### **Features and Benefits**

- Low RDS(ON) Minimizes Conduction Losses
- Fast Switching Speed Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP4025SFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

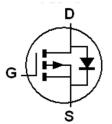
#### **Mechanical Data**

- Package: PowerDI<sup>®</sup>3333-8
- Package Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 (£3)
- Weight: 0.0172 grams (Approximate)

#### PowerDI3333-8







Device Symbol

#### **Ordering Information** (Note 4)

Part Number	Paakaga	Packing			
Fait Number	Package	Qty.	Carrier		
DMP4025SFGQ-7	PowerDI3333-8	2,000	Reel		
DMP4025SFGQ-13	PowerDI3333-8	3,000	Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



## **Marking Information**

Site 1



P40 = Product Marking Code YYWW = Date Code Marking YY = Year (ex: 21 = 2021)WW = Week (01 to 53)

Site 2



P40 = Product Type Marking Code YWX = Date Code Marking

Y = Year (ex: 1 = 2021)

W = Week (ex: a = Week 27; z Represents Week 52 and 53)

X = Internal Code (ex: U = Monday)

Date Code Key

Year	2014	 2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	4	 1	2	3	4	5	6	7	8	9	0

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Υ	Z

# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristi	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	-40		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current, V <sub>GS</sub> = -10V	(Note 6)		-7.2	
	$T_A = +70^{\circ}C$ (Note 6)	ID	-5.77	
	(Note 5)		-4.65	
Maximum Body Diode Forward Current (Note 6)		Is	-7.2	A
Pulsed Drain Current (Note 7)		I <sub>DM</sub>	-80	
Pulsed Source Current	(Note 7)	Ism	-80	

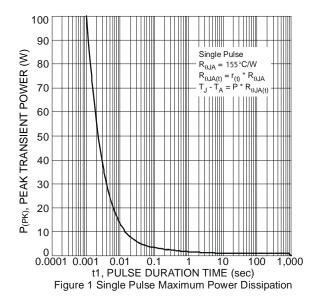
## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D-	0.81	14/	
Linear Derating Factor	(Note 6)	PD	1.95	W	
Thermal Desigtance Junction to Ambient	(Note 5)		155	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	64	3C/VV	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 6. For a device surface mounted on 25mm x 25mm FR-4 PCB with 2oz copper, in still air conditions.
- 7. Same as note (6), except the device is pulsed with D= 0.02 and pulse width 300µs.



## **Thermal Characteristics**



1 D=0.9 r(t), TRANSIENT THERMAL RESISTANCE D=0.7 D=0.3 0.1 D=0.02 0.01 D=0.005  $R_{\theta JA}(t) = r(t) * R_{\theta JA}$  $R_{\theta JA} = 64^{\circ}C/W$ D=Single Pulse Duty Cycle, D = t1 / t20.001 1E-06 1E-05 0.0001 0.001 0.01 0.1 10 100 1000 t1, PULSE DURATION TIME (sec)

Figure 2. Transient Thermal Resistance



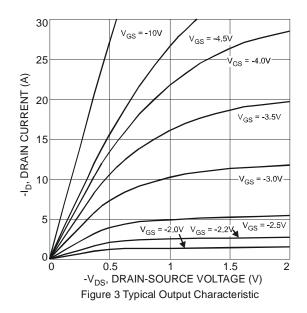
# **Electrical Characteristics** (@ $T_A = +25$ °C, unless otherwise specified.)

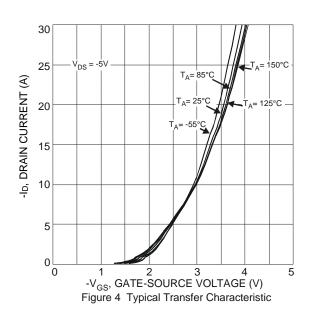
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40	_		V	$I_D = -250 \mu A$ , $V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	IDSS	_	_	-1.0	μΑ	$V_{DS} = -40V$ , $V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	Vgs(TH)	-0.8	-1.3	-1.8	V	$I_D = -250\mu A$ , $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 8)	Process		18	25	mΩ	$V_{GS} = -10V, I_D = -3A$	
Static Dialit-Source Off-Resistance (Note 6)	RDS(ON)		30	45	11122	$V_{GS} = -4.5V$ , $I_{D} = -3A$	
Forward Transconductance (Notes 8 & 9)	<b>g</b> fs	_	16.6		S	$V_{DS} = -5V, I_{D} = -3A$	
Diode Forward Voltage (Note 8)	VsD	_	-0.7	-1.0	V	Is = -1A, V <sub>G</sub> S = 0V	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	1643	_		.,	
Output Capacitance	Coss	_	179	_	pF	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1MHz	
Reverse Transfer Capacitance	Crss	_	128	_		1 = 11011 12	
Gate Resistance	$R_g$	_	6.43	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (Note 10)	$Q_g$	_	14.0	_		V <sub>GS</sub> = -4.5V	
Total Gate Charge (Note 10)	Qg	_	33.7	_	~	V <sub>DS</sub> = -20V	
Gate-Source Charge (Note 10)	Qgs	_	5.5	_	nC	$V_{GS} = -10V$ $I_{D} = -3A$	
Gate-Drain Charge (Note 10)	Q <sub>gd</sub>	_	7.3				
Turn-On Delay Time (Note 10)	tD(ON)	_	6.9	_			
Turn-On Rise Time (Note 10)	t <sub>R</sub>	_	14.7		V <sub>DD</sub> = -20V, V <sub>GS</sub> = -10V		
Turn-Off Delay Time (Note 10)	tD(OFF)	_	53.7		ns	I <sub>D</sub> = -3A	
Turn-Off Fall Time (Note 10)	tF	_	30.9				

Notes:

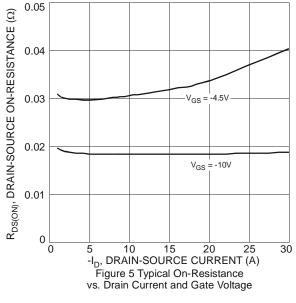
- 8. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s;$  duty cycle  $\leq 2\%.$
- 9. For design aid only, not subject to production testing.10. Switching characteristics are independent of operating junction temperatures.

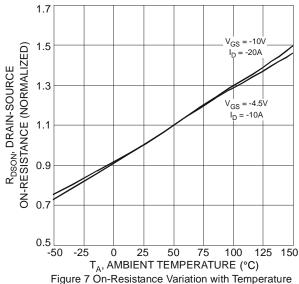
## **Typical Characteristics**

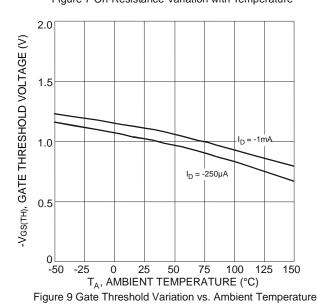


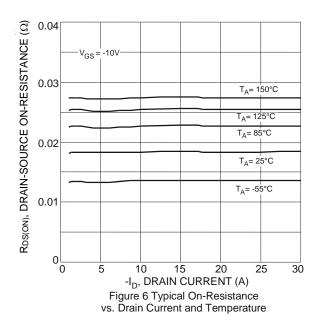












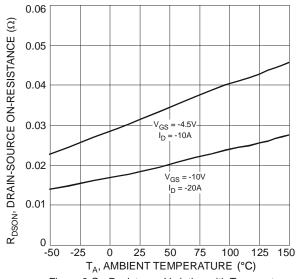
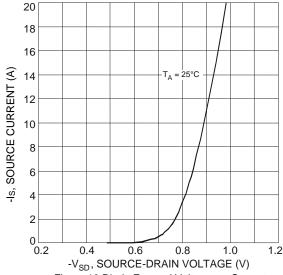
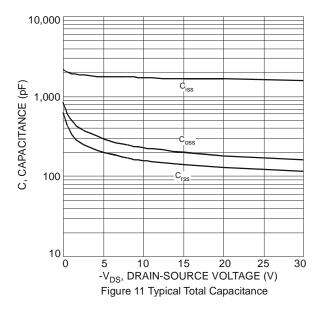


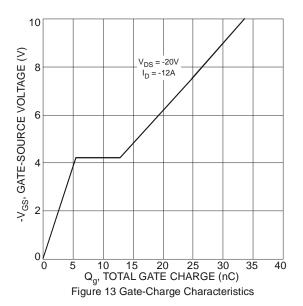
Figure 8 On-Resistance Variation with Temperature

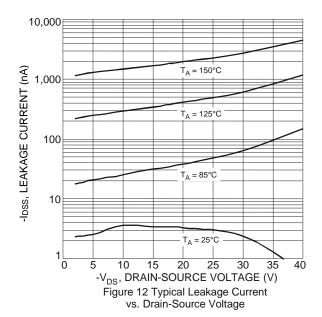


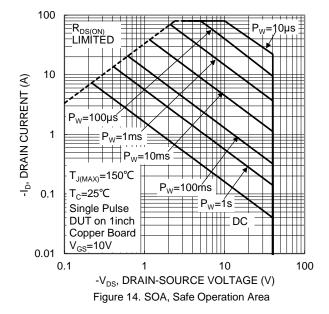










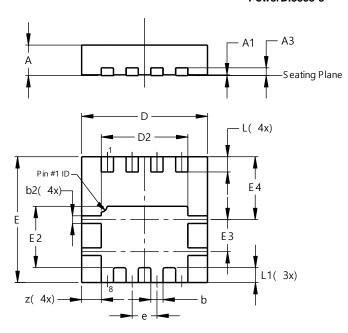




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8

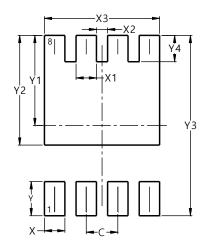


	Powerl	DI3333-	-8
Dim	Min	Max	Тур
Α	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	_	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
е	-	_	0.65
L	0.35	0.45	0.40
L1	-	_	0.39
Z	_	_	0.515
All	Dimens	sions ir	n mm

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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